This Sheet Has Been Replaced





# TERMINATION STRUCTURE FOR SEMICONDUCTOR DEVICES AND PROCESS FOR MANUFACTURE THEREOF


## ABSTRACT OF THE DISCLOSURE

A termination structure for semiconductor devices and a process for fabricating the termination structure are described which prevent device breakdown at the peripheries of the device. The termination structure includes a polysilicon field plate located atop a portion of a field oxide region and which, preferably, overlays a portion of the base region. The field plate may also extend slightly over the edge of the field oxide to square off the field oxide taper. The termination structure occupies minimal surface area of the chip and is fabricated without requiring additional masking steps.